

PixFEL: high resolution, fast, multi-tier detectors for diffraction imaging at next generation X-ray FELs









Pavia

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on behalf of the PixFEL collaboration



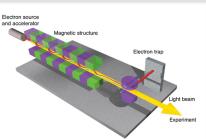


Trento

Introduction

FELs provide high intensity beam of ultrafast X-rays

- energy range: 100 eV to >10 keV (λ from 10 nm to 0.1 nm)
- pulse duration: femtoseconds to picoseconds
- repetition rate: 10 Hz (continuous mode) to 5 MHz (burst mode)
- peak brightness may exceed 10³³ ph s⁻¹ mm⁻² mrad⁻¹



Novel experimental capabilities at the frontier of structural biology chemistry material science atomic and molecular science These new sources are driving the state of the art of X-ray science and are shaping the requirements for new

PixFEL: advanced instrumentation for X-ray diffraction imaging Advanced interconnection technologies for high density integration Slim/active edge sensors for minimum dead area active edge sensor good efficiency from 1 Field plate 5 um keV (optimized entrance window) up to 10 keV (450 um thickness) n/p gap high density interconnect low density Trench edge bond peripheral TSVs n⁻ substrate low density bonding minimize the gap between the sensor and the edge while avoiding leakage g bit resolution (effective), 5 MHz sampling rate high density TSVs readout active edge wide dynamic range (1 to 10000 photons), single photon sensitivity burst and front-end+ADC memory+digital readout 10⁴ dynamic range, 5 MHz sample dynamic signal large bias voltage compression rate front-end in 65 nm CMOS to mitigate plasma fast time-variant thick substrate and processing and thin entrance window conversion for best collection efficiency single photon 4 GR, 2.4 um junction depth, 300 nm thick oxide resolution total gap 155 um 1.0-0.2 V <2% dead area Ampli with signal SAR ADC Time-variant filter V-I converter compression

Potential impact

The PixFEL project will tackle the growing need for new and advanced instrumentation able to take advantage of the outstanding features of FELs at different levels

- the availability of state-of-the art instrumentation will facilitate progress in strategic fields of life science and materials science and, ultimately, in key sectors like health care, green transportation and quality of life
- because of the aggressive specifications of the developed sensors, the knowledge gained through this project will also benefit other fields of radiation instrumentation, where fast, minimum dead area, intelligent pixel sensors are needed, such as particle trackers in high energy physics experiments, beam monitors for hadrontherapy, devices for medical radio-diagnostic systems
- the program is expected to spawn significant advancements in microelectronic circuit design for imaging sensors this will be achieved also by means of the application of state-of-the art interconnection processes and pixel sensor fabrication technologies to scientific instrumentation

